# Power MOSFET 35V, $37m\Omega$ , 6A, Single N-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

# Features

- Low On-Resistance
- 4V drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance

#### **Typical Applications**

- DC/DC Converter
- Current Balance Switch for Backlight

#### **SPECIFICATIONS**

#### **ABSOLUTE MAXIMUM RATING** at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	35	٧
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ID	6	Α
Drain Current (Pulse) PW ≤ 10µs, duty cycle ≤ 1%	IDP	24	А
Power Dissipation When mounted on ceramic substrate (1200mm² × 0.8mm)	PD	1.6	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (1200mm² × 0.8mm)	$R_{ heta JA}$	78.1	°C/W

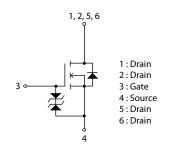


## ON Semiconductor®

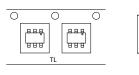
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VDSS	R <sub>DS</sub> (on) Max	ID Max
	37mΩ@ 10V	
35V	61mΩ@ 4.5V	6A
	73mΩ@ 4V	

# ELECTRICAL CONNECTION N-Channel



# PACKING TYPE : TL MARKING





#### ORDERING INFORMATION

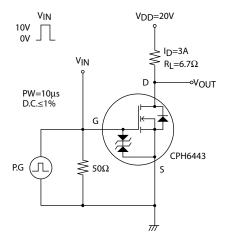
See detailed ordering and shipping information on page 5 of this data sheet.

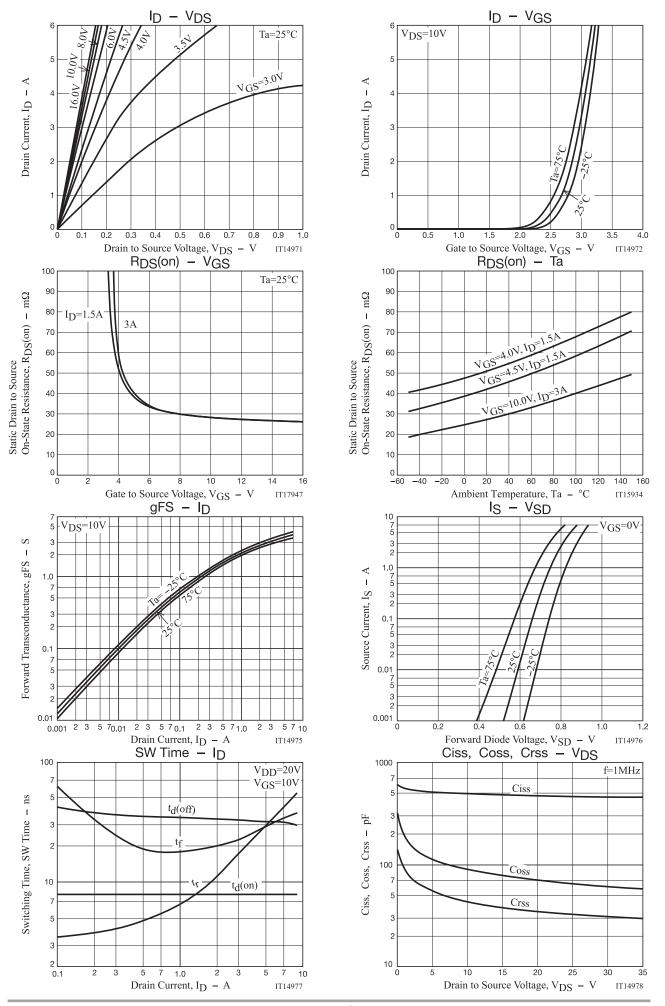
**ELECTRICAL CHARACTERISTICS** at Ta = 25°C (Note 2)

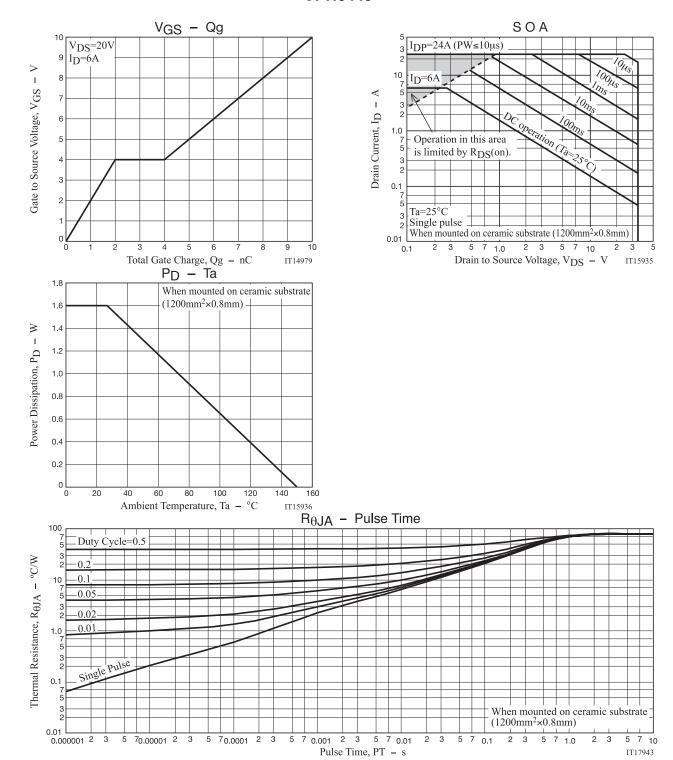
Parameter	Cumbal	Conditions	Value			Unit	
Parameter	Symbol	Conditions	min	typ	max	Offic	
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =35V, V <sub>GS</sub> =0V			1	μΑ	
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ	
Gate Threshold Voltage	V <sub>G</sub> S(th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V	
Forward Transconductance	gFS	V <sub>DS</sub> =10V, I <sub>D</sub> =3A		2.9		S	
	R <sub>DS</sub> (on)1	I <sub>D</sub> =3A, V <sub>GS</sub> =10V		28	37	$m\Omega$	
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =1.5A, V <sub>GS</sub> =4.5V		43	61	$m\Omega$	
Resistance	R <sub>DS</sub> (on)3	I <sub>D</sub> =1.5A, V <sub>GS</sub> =4V		52	73	$m\Omega$	
Input Capacitance	Ciss			470		pF	
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		70		pF	
Reverse Transfer Capacitance	Crss			35		pF	
Turn-ON Delay Time	t <sub>d</sub> (on)			8		ns	
Rise Time	tr	Can appoint Toot Circuit		17		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		32		ns	
Fall Time	tf			22		ns	
Total Gate Charge	Qg			10		nC	
Gate to Source Charge	Qgs	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		2		nC	
Gate to Drain "Miller" Charge	Qgd			2		nC	
Forward Diode Voltage	V <sub>SD</sub>	IS=6A, VGS=0V		0.84	1.2	V	

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **Switching Time Test Circuit**







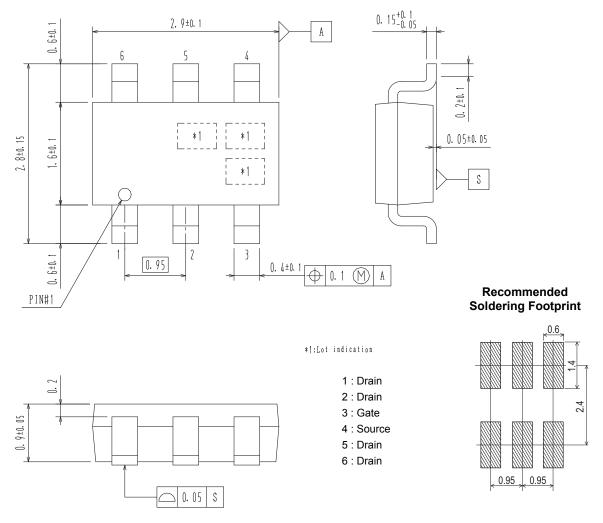
IT17943

#### PACKAGE DIMENSIONS

unit: mm

### СРН6

CASE 318BD ISSUE O



#### ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)	
CPH6443-TL-H	ZV	CPH6	3,000 / Tape & Reel	
CPH6443-TL-W	ZV	(Pb-Free / Halogen Free)		

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage: Since the CPH6443 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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